

nitride layer is removed, usually by a plasma etching process, and finally the remaining unexposed part of the resist is removed, e.g., by ashing the resist in an oxygen plasma.

*Dread* Nitride structuring is performed first on the front side of the wafer, as shown in Part 1; this structuring yields structured nitride layer 25. Unstructured nitride layer 24 is still imaged on the back side.

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IN THE CLAIMS:

Please cancel claims 1-13

Please add the following new claims:

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*Sub Ex 01* 14. (New) A method of etching a wafer, comprising the steps of:

providing a wafer having a surface and edge areas;  
dividing the surface of the wafer into positive areas and negative areas, the negative areas including the edge areas of the wafer;

*D2* providing the negative areas with a first passivation layer to protect the negative areas from a subsequent wet chemical etching process;

providing at least one of the positive areas with a second passivation layer having a thickness that is less than a thickness of the first passivation layer;

etching the wafer in the wet chemical etching process; and

removing the first passivation layer.

15. (New) The method according to claim 14, wherein the dividing step includes the sub-steps of:

applying a nitride layer; and

structuring the nitride layer using a photoresist technique, wherein the positive areas of the surface of the wafer are defined by a part of the surface covered with the nitride layer.